

60V (D-S) 小信号MOSFET

UM2362S SOT23-3

UM2362P SOT323

描述

UM2362 是一款低阈值 N 沟道 MOSFET，具有低导通电阻、高可靠性和稳定性，以及快速开关能力和高饱和电流。这一优势为设计师提供了适用于电池和负载管理应用的极高效器件。该器件采用节省空间、外形小巧的 SOT23-3 或 SOT323 封装。

应用

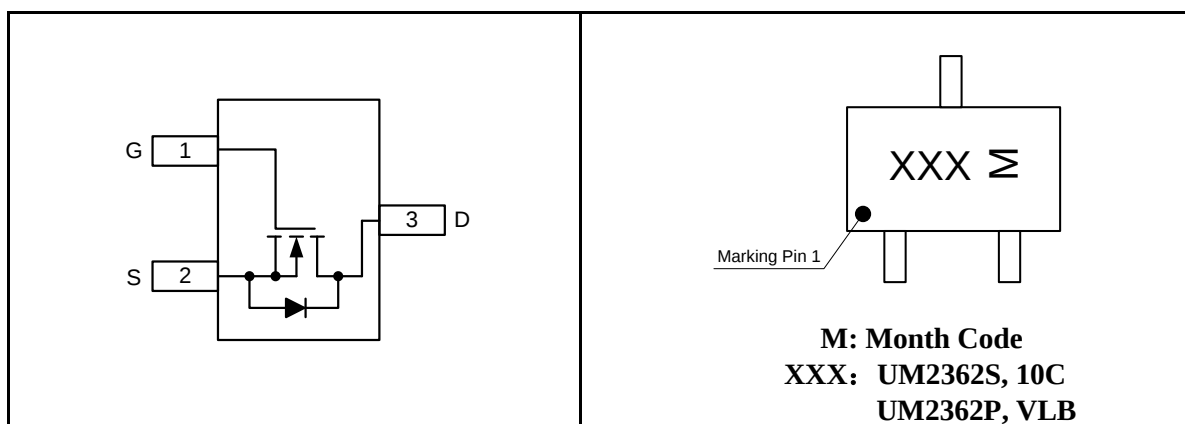
- 电池组
- 电池供电的便携式设备
- 手机和无线电话

特性

- 漏源电压（最大）：60V
- 低导通电阻（典型值）：
1.2Ω@V_{GS}=10V
1.7Ω@V_{GS}=5V
- 持续漏极电流（最大）：
115mA@25℃

引脚配置

顶部视图



订购信息

芯片型号	封装类型	丝印编码	发货数量
UM2362S	SOT23-3	10C	3000pcs/7 Inch Tape & Reel
UM2362P	SOT323	VLB	3000pcs/7 Inch Tape & Reel

Absolute Maximum Ratings (T_{amb}=25 °C)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	115	mA
P _D	Power Dissipation	200	mW
T _J	Junction Temperature	+150	°C
T _{stg}	Storage Temperature	-55 to +150	°C

Electrical Characteristics (T_{amb}=25 °C, unless otherwise noted)

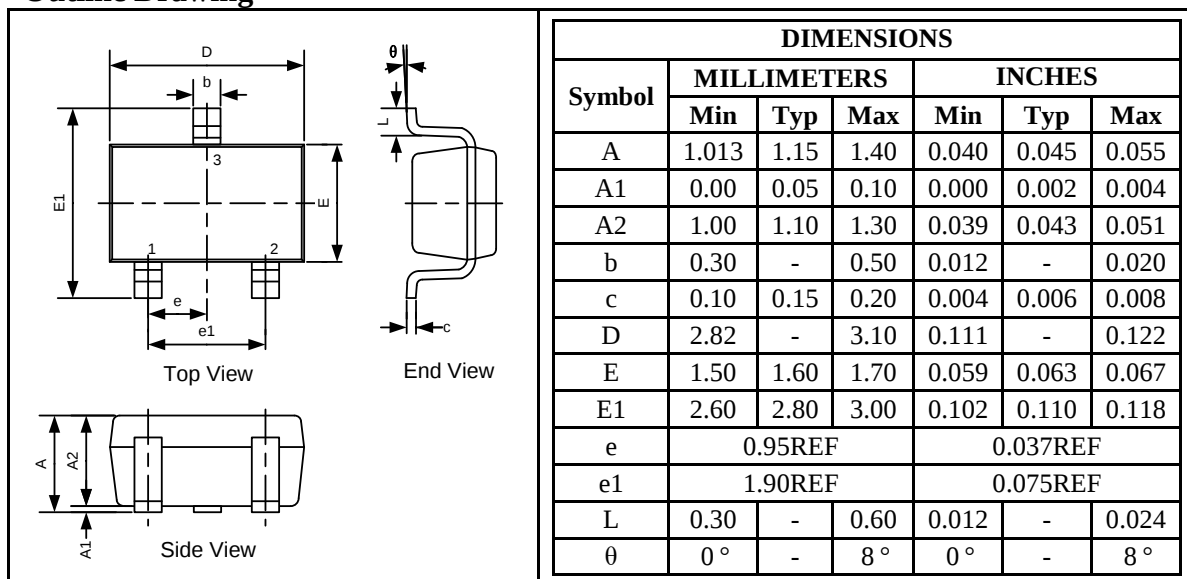
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =10μA	60			V
		V _{GS} =0V, I _D =3mA	60			
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			1	μA
I _{GSS}	Gate-to-Source Leakage Current	V _{GS} = ±20V, V _{DS} =0V			±100	nA
On Characteristics						
R _{DS(ON)*}	Static Drain-to-Source On-Resistance	V _{GS} =10V, I _D =500mA		1.2	7.5	Ω
		V _{GS} =5V, I _D =50mA		1.7	7.5	
V _{GS(TH)*}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1		2.5	V
I _{D(ON)*}	Drain-to-Source On Current	V _{GS} =10V, V _{DS} =7V	500			mA
V _{DS(ON)*}	Drain-to-Source On Voltage	V _{GS} =10V, I _D =500mA			3.75	V
		V _{GS} =5V, I _D =50mA			0.375	
g _{fs} *	Forward Transconductance	V _{DS} =10V, I _D =200mA	80			mS
Drain-Source Diode Characteristics and Maximum Ratings						
V _{SD}	Forward Diode Voltage	V _{GS} =0V, I _S =115mA			1.2	V

*Pulse test: Pulse Width≤300μs, Duty Cycle≤2%

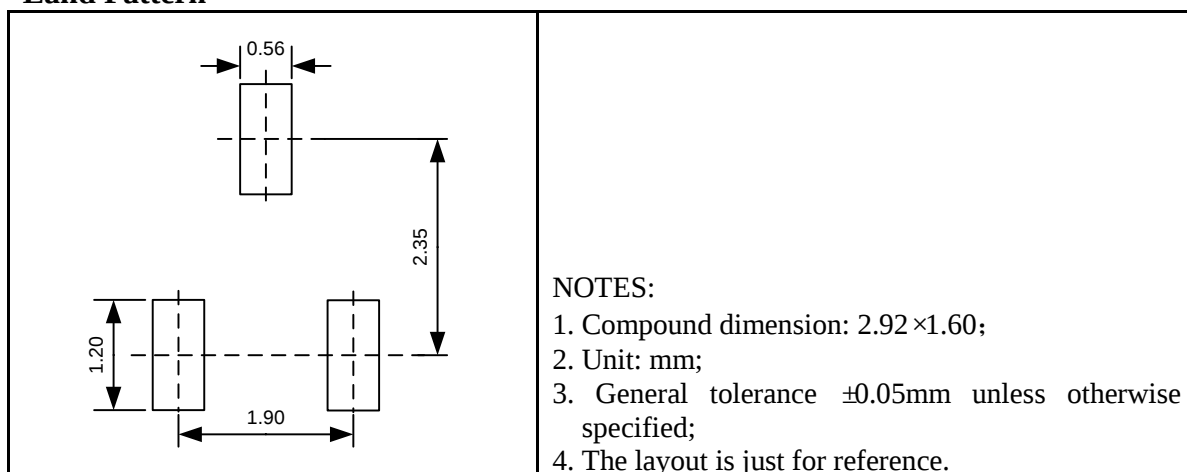
Package Information

UM2362S SOT23-3

Outline Drawing



Land Pattern

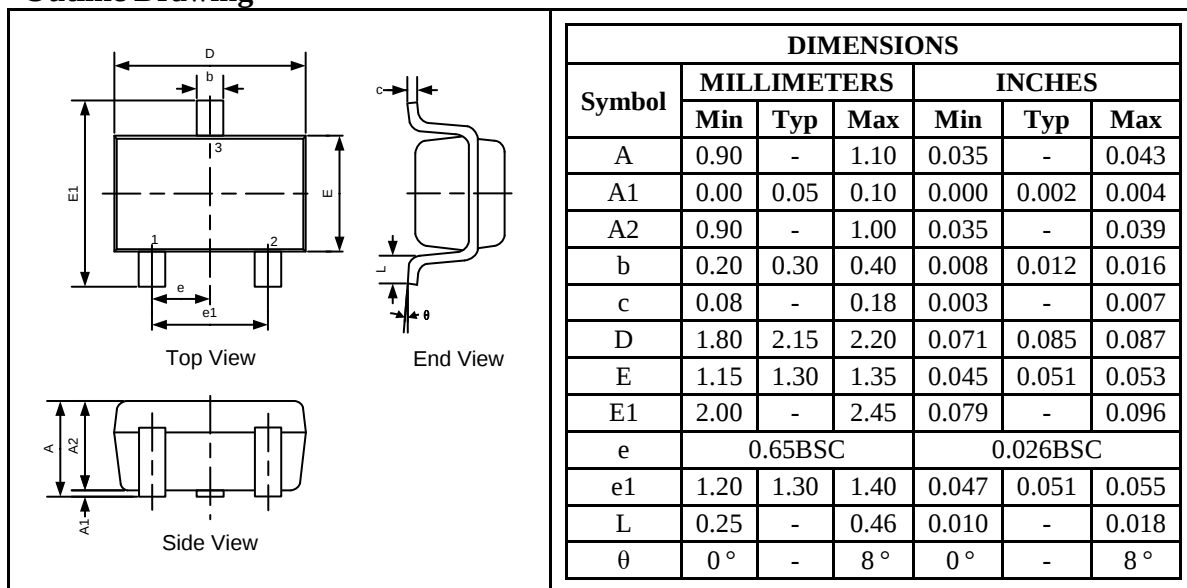


Tape and Reel Orientation

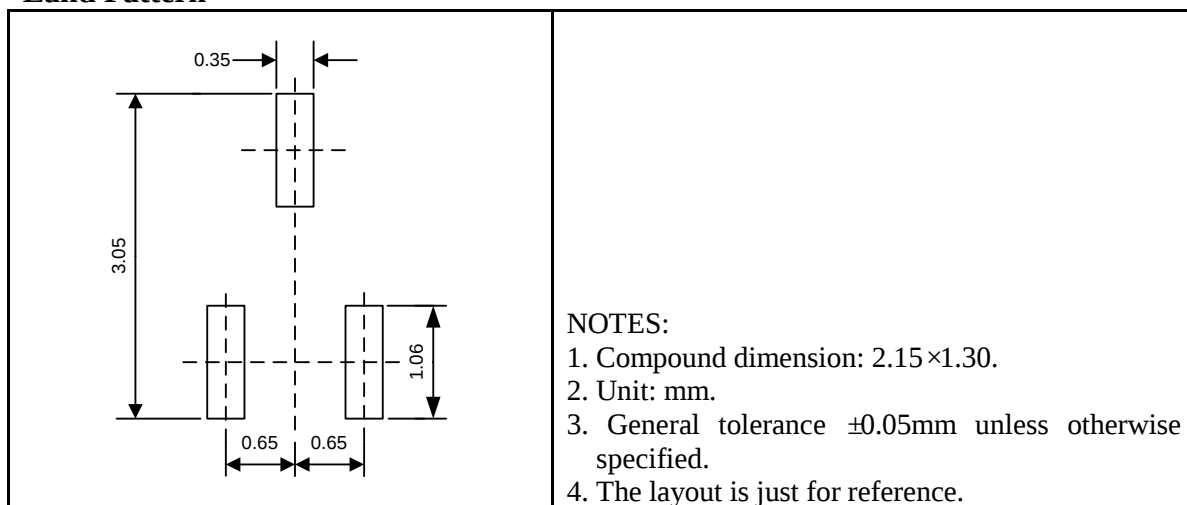


UM2362P SOT323

Outline Drawing



Land Pattern



Tape and Reel Orientation



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